

PCN Number:	20130401005		PCN Date:	04/04/2013	
Title:	Transfer of select devices in the Vertical Diode-BD process node to CFAB Facility				
Customer Contact:	PCN Manager	Phone:	+1(214)480-6037	Dept: Quality Services	
Proposed 1st Ship Date:	07/04/2013	Estimated Sample Availability:	Date available upon sample request		
Change Type:					
<input type="checkbox"/>	Assembly Site	<input type="checkbox"/>	Assembly Process	<input type="checkbox"/>	Assembly Materials
<input type="checkbox"/>	Design	<input type="checkbox"/>	Electrical Specification	<input type="checkbox"/>	Mechanical Specification
<input type="checkbox"/>	Test Site	<input type="checkbox"/>	Packing/Shipping/Labeling	<input type="checkbox"/>	Test Process
<input type="checkbox"/>	Wafer Bump Site	<input type="checkbox"/>	Wafer Bump Material	<input type="checkbox"/>	Wafer Bump Process
<input checked="" type="checkbox"/>	Wafer Fab Site	<input type="checkbox"/>	Wafer Fab Materials	<input checked="" type="checkbox"/>	Wafer Fab Process

PCN Details

Description of Change:

This change notification is to announce the transfer of select devices in the Vertical Diode – Bi-Directional process node from HIJI to the CFAB facility. This will also include a wafer diameter change from 6" to 8".

Current	New
Site, process, wafer dia.	Site, process, wafer dia.
HIJI/ VD-BD, 150mm	CFAB/ VD-BD, 200mm

Reason for Change:

Continuity of Supply. HIJI site shutdown.

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Changes to product identification resulting from this PCN:

Current		
Chip Site	Chip site code (20L)	Chip country code (21L)
HIJI	HIJ	JPN
New		
Chip Site	Chip site code (20L)	Chip country code (21L)
CFAB	CU3	CHN

Sample product shipping label (not actual product label)

 TEXAS INSTRUMENTS MADE IN: Malaysia 2DC: 20: MSL 2 /260C/1 YEAR SEAL DT MSL 1 /235C/UNLIM 03/29/04 OPT: ITEM: 39 LBL: 5A (L)T0:1750	 G4	(1P) SN74LS07NSR (Q) 2000 (D) 0336 (31T) LOT: 3959047MLA (4W) TKY (1T) 7523483SI2 (P) (2P) REV: (V) 003317 (20L) CSO: SHE (21L) CCO:USA (22L) ASO: MLA (23L) AOO: MYS
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Product Affected:		
TPD1E10B06DPYR	TPD1E10B09DPYR	TPD1E6B06DPLR
TPD1E10B06DPYT	TPD1E10B09DPYT	TPD1E6B06DPLT

Qualification Plan:				
This qualification has been developed for the validation of this change. The qualification data will validate that the proposed change meets the applicable released technical specifications.				
Qualification Schedule:	Start:	03/2013	End:	End of 07/2013
Qual Vehicle: TPD4E101DPWR				
Wafer Fab Site:	CFAB	Metallization:	AICuTiW	
Wafer Fab Process:	VD	Wafer Diameter:	200mm	
Qualification:	<input checked="" type="checkbox"/> Plan		<input type="checkbox"/> Test Results	
Reliability Test	Conditions	Sample Size/Fails		
		Lot#1	Lot#2	Lot#3
Preconditioning	-	231/0	231/0	231/0
HTOL High Temp Op Life	150C (300 Hrs)	77/0	-	-
Electrical Characterization	-	30/0	30/0	30/0
High Temp. Storage Bake	170C (420 Hrs)	77/0	77/0	77/0
**Biased HAST	130C/85%RH (96 Hrs)	77/0	77/0	77/0
**Autoclave 121C	121C, 2 atm (96 Hrs)	77/0	77/0	77/0
**T/C -65C/150C	-65C/+150C (500 Cycles)	77/0	77/0	77/0
ESD CDM	500V	3/0	3/0	3/0
ESD HBM	1000V	3/0	3/0	3/0
**Preconditioning: Level 1-260C				

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com